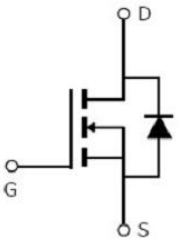
V_{DSS}	40V
R_{DS}(on)	2.4mΩ(typ.)
I_D	200A



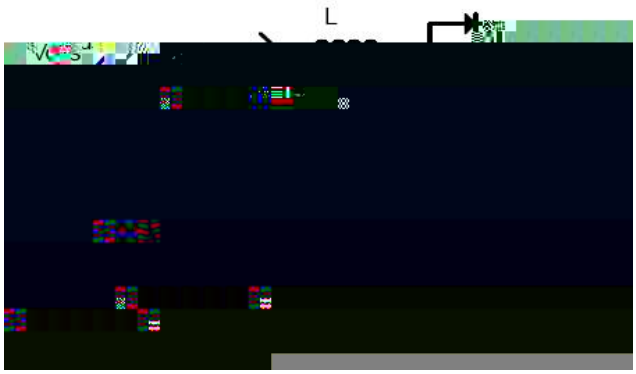
Advanced MOSFET process technology
Special designed for PWM, load switching and general purpose applications
Ultra low on-resistance with low gate charge
Fast switching and reverse body recovery
175 operating temperature

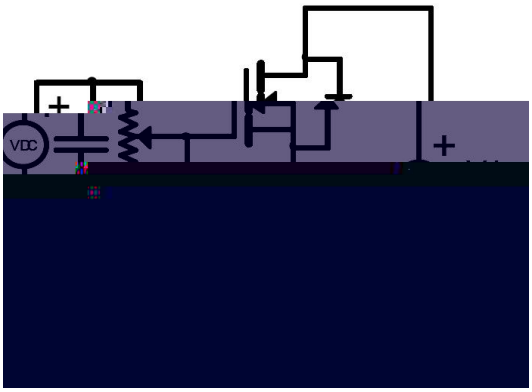
It utilizes the latest processing techniques to achieve the high cell density and reduces the on-resistance with high repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in power switching application and a wide variety of other applications.

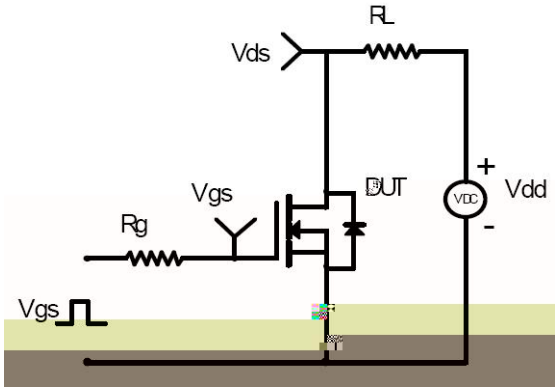
I_D @ TC = 25°C	Continuous Drain Current, V_{GS} @ 10V	200	A
I_D @ TC = 100°C	Continuous Drain Current, V_{GS} @ 10V	135	
I_{DM}	Pulsed Drain Current	750	
P_D @TC = 25°C	Power Dissipation	220	W
	Linear Derating Factor	1.5	W/°C
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-to-Source Voltage	± 24	V
E_{AS}	Single Pulse Avalanche Energy @ L=0.3mH	912	mJ
I_{AS}	Avalanche Current @ L=0.3mH	78	A
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	°C

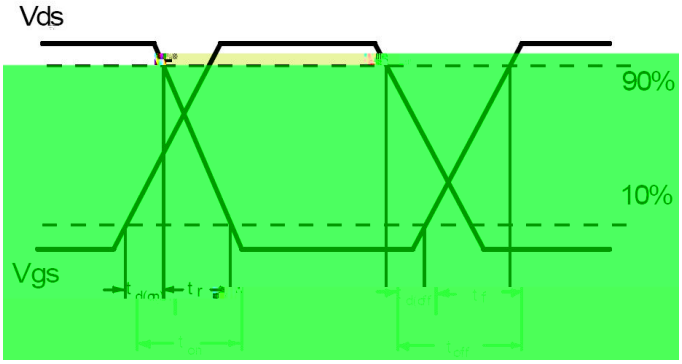
$R_{\theta JC}$	Junction-to-case	—	0.62	/W
$R_{\theta JA}$	Junction-to-ambient (t ≤ 10s)	—	60	/W
	Junction-to-Ambient (PCB mounted, steady-state)	—	40	/W

@T_A=25 unless other







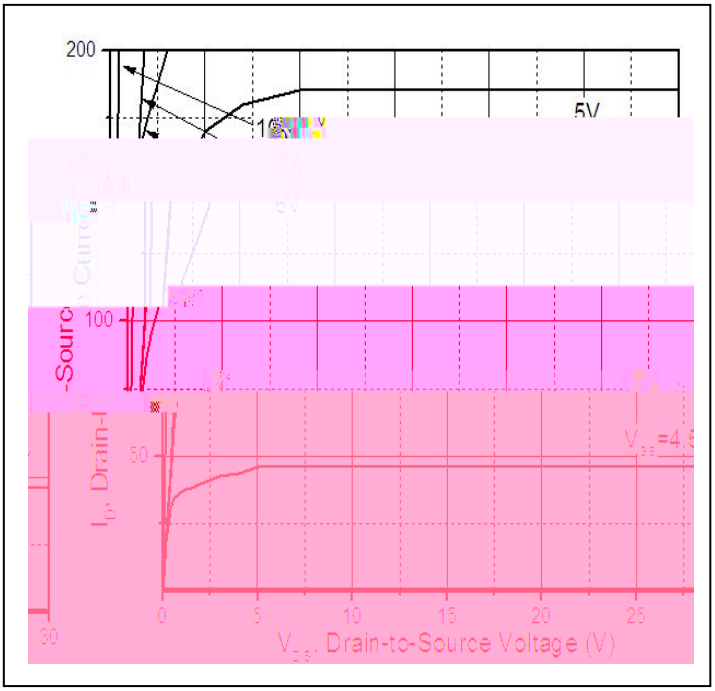


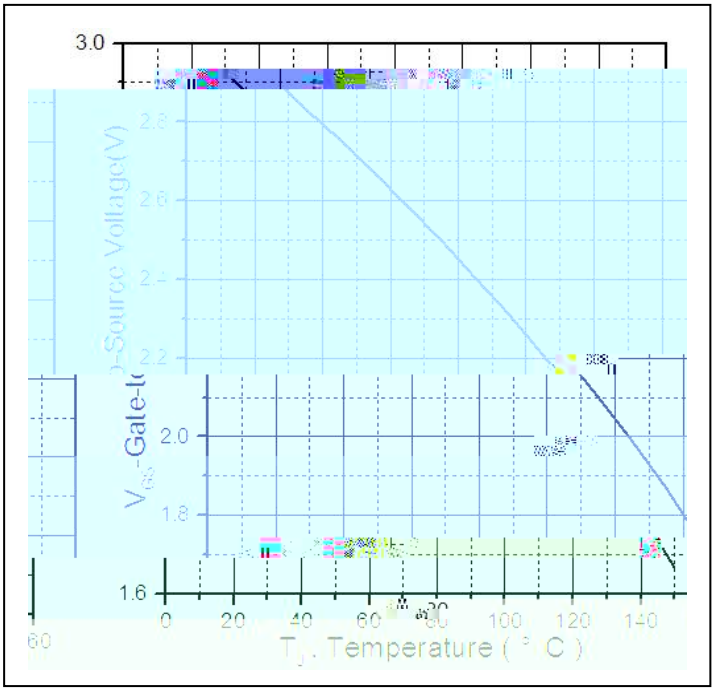
Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 75A.

Repetitive rating; pulse width limited by max junction temperature.

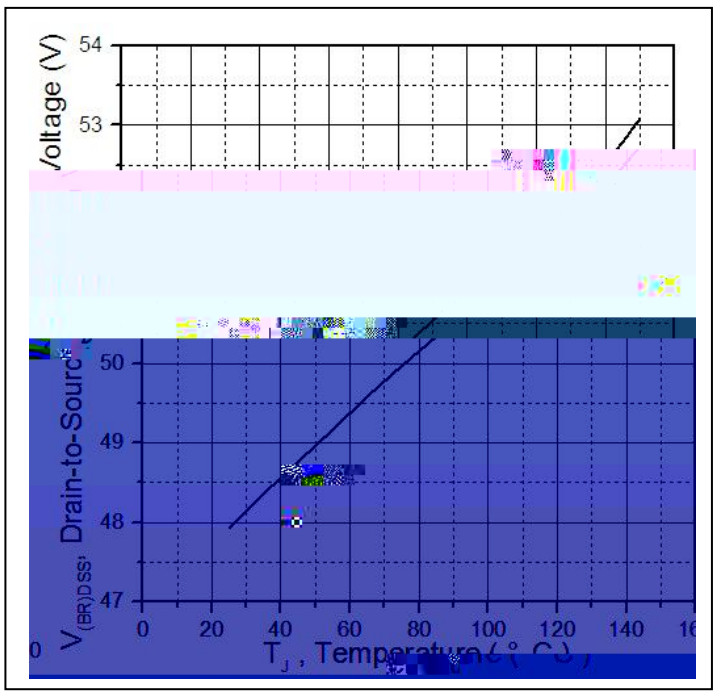
The power dissipation PD is based on max junction temperature, using junction-to-case thermal resistance.

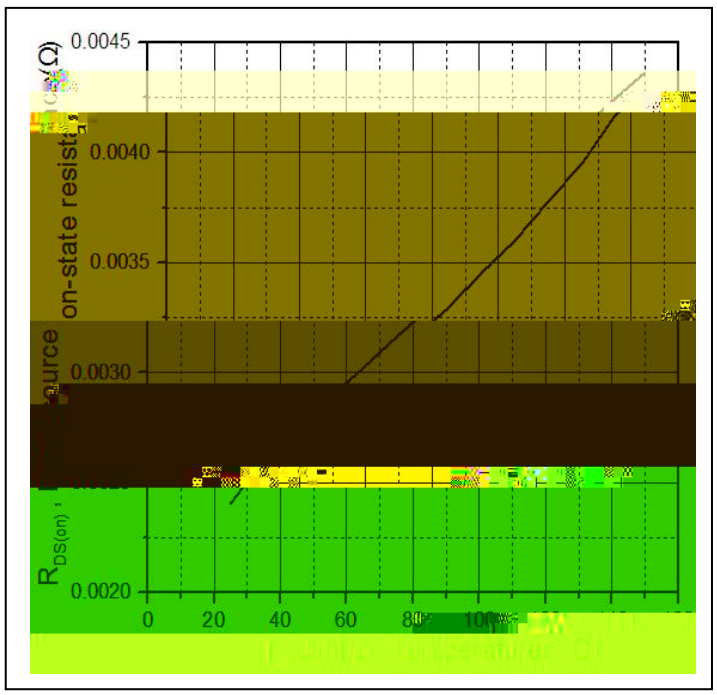
The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with TA =25°C

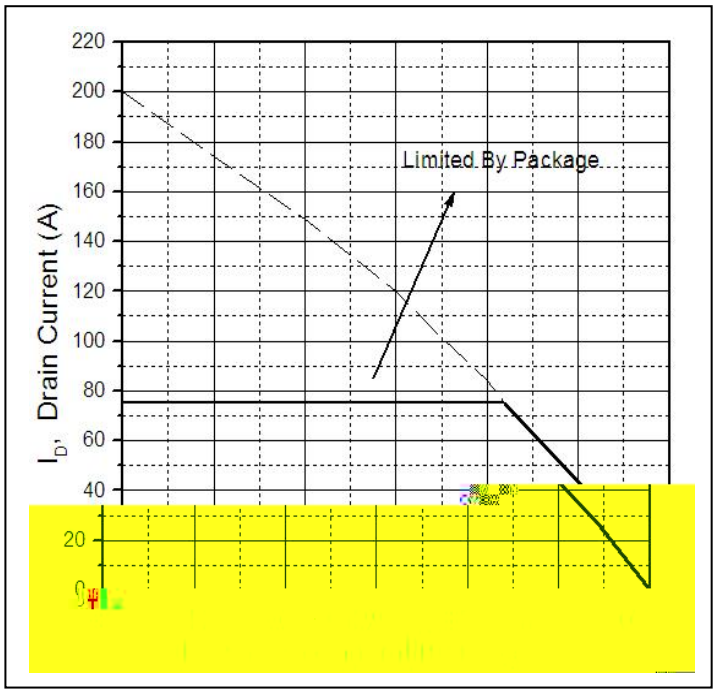


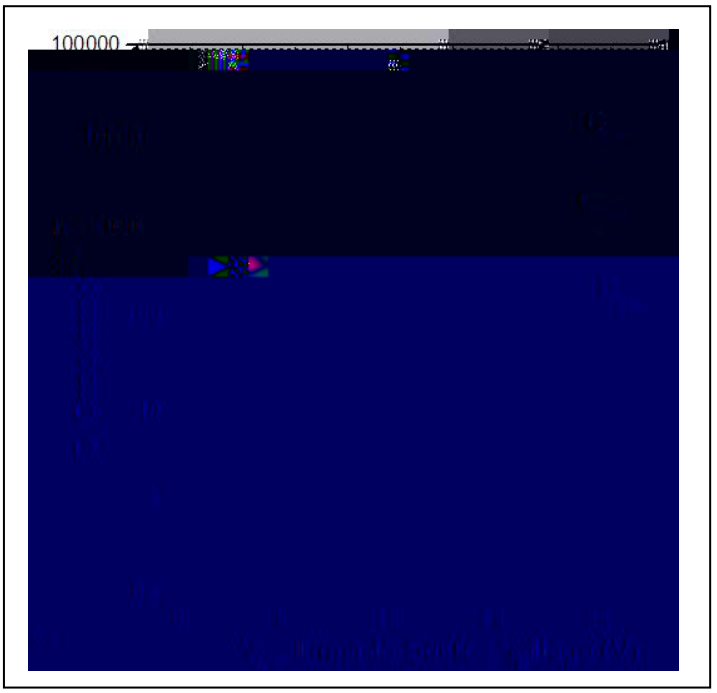


Gate to source cut-off Voltage






220
200
180
160
140
120
100
80
60
40
20
0
Limited By Package
I_D, Drain Current (A)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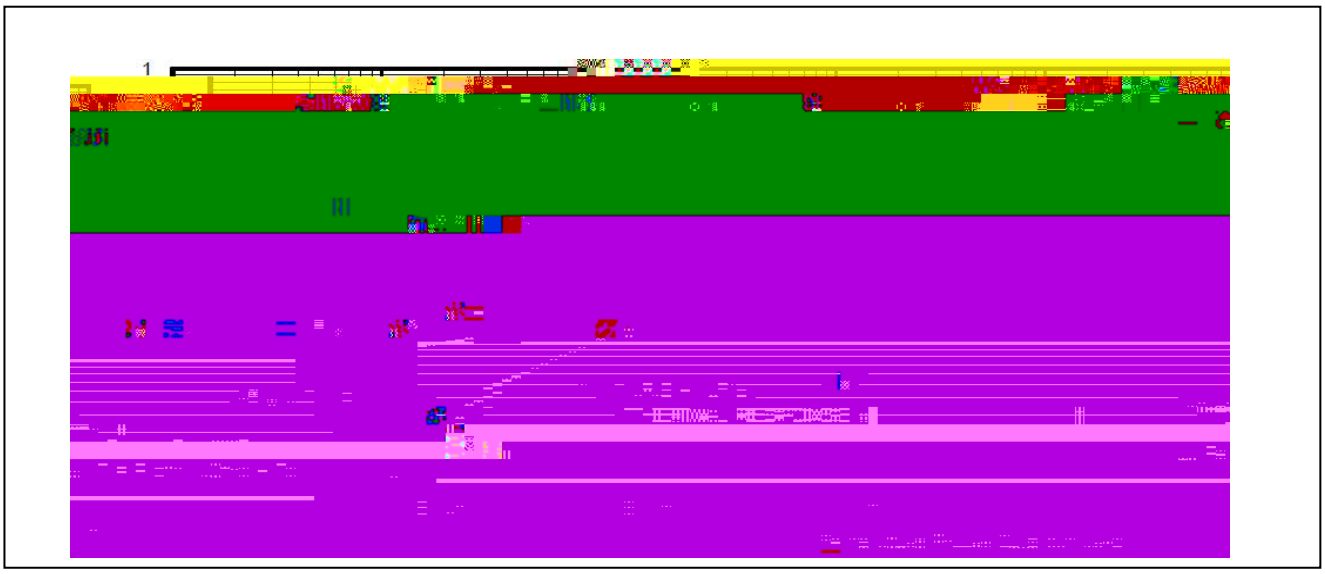
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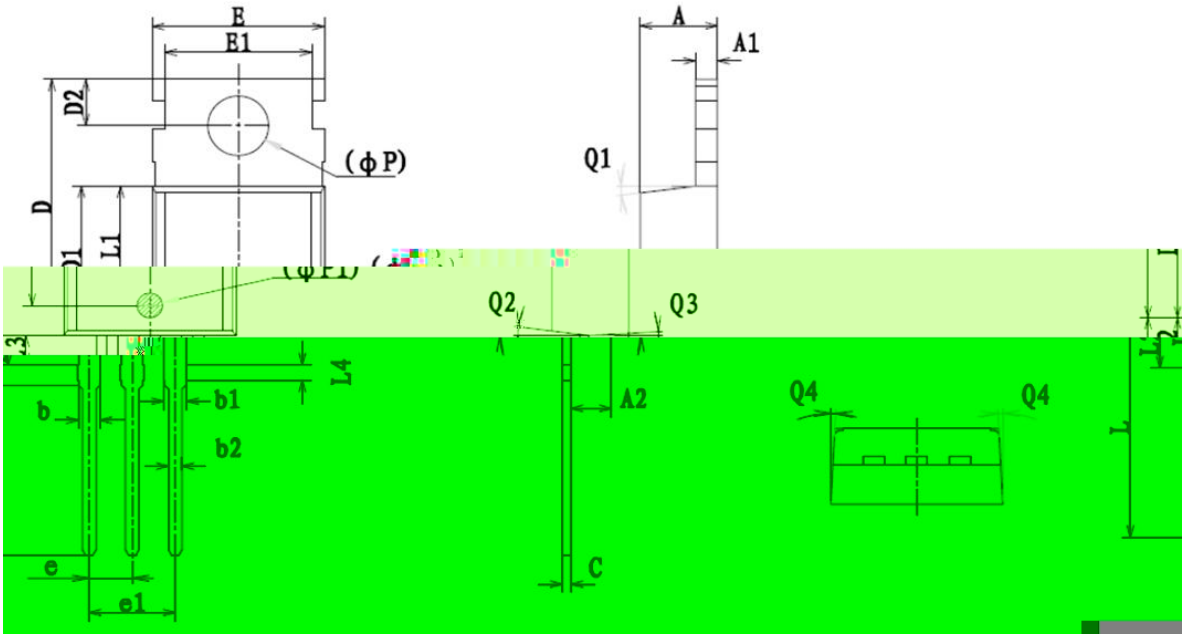
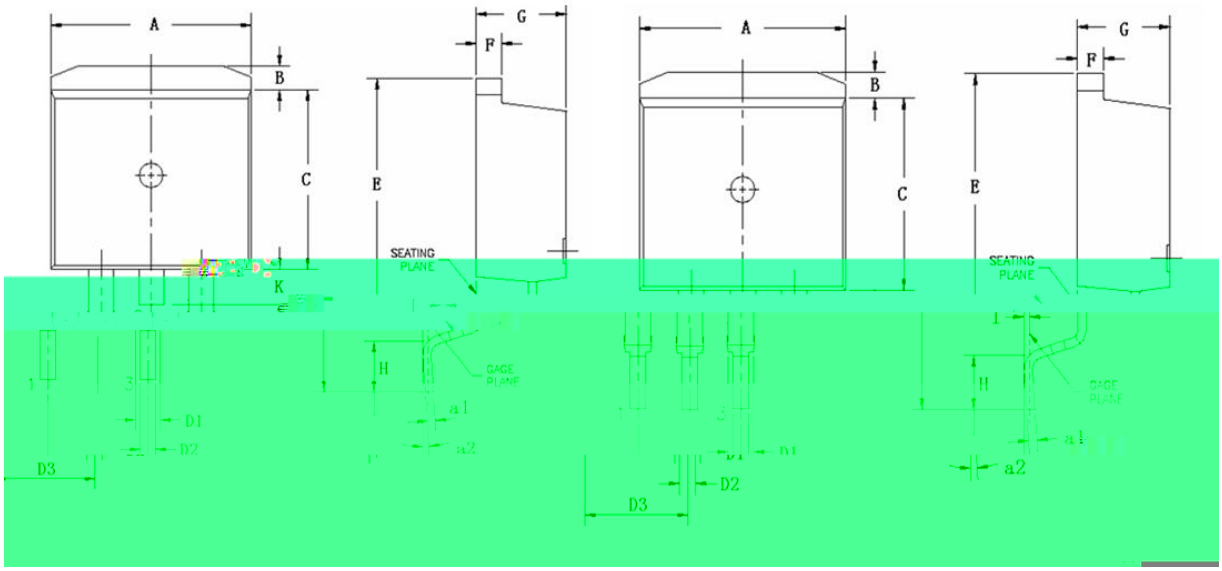


Symbol	Dimension In Millimeters			Dimension In Inches		
	Min					



Symbol	Dimension In Millimeters		Dimension In Inches	
	Min	Max	Min	Max
A	9.660	10.280	0.380	0.405
B	1.020	1.320	0.040	0.052
C	8.590	9.400	0.338	0.370
D1	1.100		0.043	
D2	0.700	0.950	0.028	0.037
D3	5.080 (TYP)		0.200 (TYP)	
E	15.090	15.390	0.594	0.606
F	1.150	1.400	0.045	0.055
G	4.300	4.700	0.169	0.185

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